BYV410-600

Enhanced ultrafast dual rectifier diode

Rev. 01 — 29 June 2009

Product data sheet

1. Product profile

1.1 General description

Enhanced ultrafast dual rectifier diode in a SOT78 (TO-220AB) plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Low on state losses

- Low thermal resistance
- Soft recovery characteristic minimizes power consuming oscillations

1.3 Applications

- Dual mode (DCM and CCM) PFC
- Power Factor Correction (PFC) for Interleaved Topology

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{O(AV)}	average output current	square-wave pulse; δ = 0.5; $T_{mb} \le 92$ °C; both diodes conducting; see Figure 1; see Figure 2	-	-	20	Α
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V;}$ $dI_F/dt = 100 \text{ A/µs;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 5}}{\text{ C}}$	-	20	35	ns
Q _r	recovered charge	$I_F = 1 A$; $V_R = 30 V$; $dI_F/dt = 100 A/\mu s$	-	15	28	С
Static ch	aracteristics					
V_{F}	forward voltage	$I_F = 10 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	1.3	1.9	V
		$I_F = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 4	-	1.4	2.1	V



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode	mb	A1
3	A2	anode 2		<u> </u>
mb	К	mounting base; cathode		sym125
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV410-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{O(AV)}	average output current	square-wave pulse; δ = 0.5; $T_{mb} \le 92$ °C; both diodes conducting; see Figure 1; see Figure 2	-	20	Α
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 µs; T _{mb} ≤ 108 °C; per diode	-	20	Α
I _{FSM}	non-repetitive peak	t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	132	Α
	forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	120	Α
T _{stg}	storage temperature		-40	150	°C
T _i	junction temperature		-	150	°C

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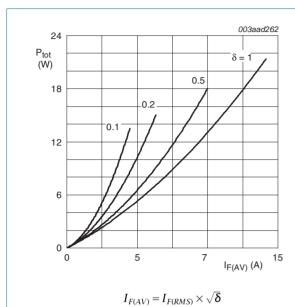


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

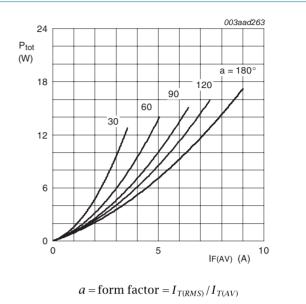


Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; per diode; see Figure 3	-	-	2.4	K/W
		with heatsink compound; both diodes conducting	-	-	1.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	60	-	K/W

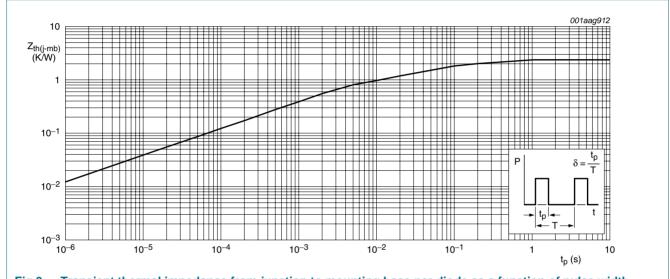


Fig 3. Transient thermal impedance from junction to mounting base per diode as a function of pulse width

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6. Characteristics

Table 6. Characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	I _F = 10 A; T _j = 150 °C	-	1.3	1.9	V
		$I_F = 10 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 4	-	1.4	2.1	V
I _R	reverse current	V _R = 600 V	-	13	50	μΑ
		V _R = 600 V; T _j = 100 °C	-	1	1.5	mA
Dynamic	characteristics					
Qr	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	15	28	С
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 5	-	20	35	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; see Figure 5	-	1.4	1.9	Α
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; see Figure 6	-	3.2	-	V

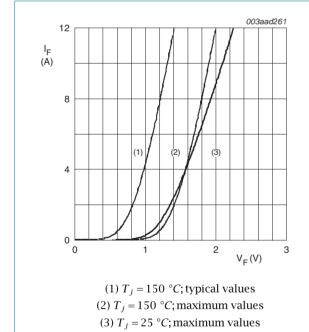


Fig 4. Forward current as a function of forward voltage

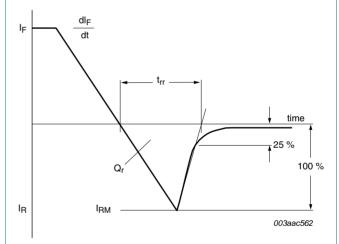
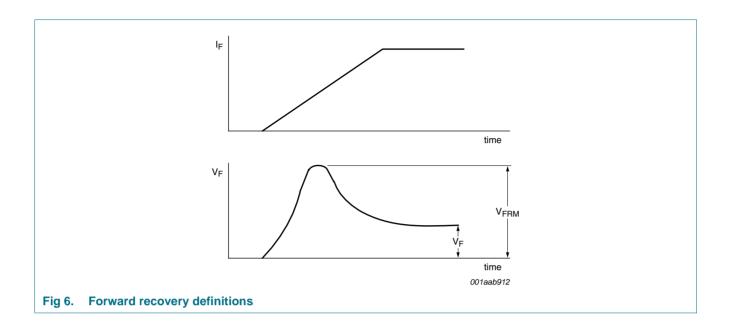


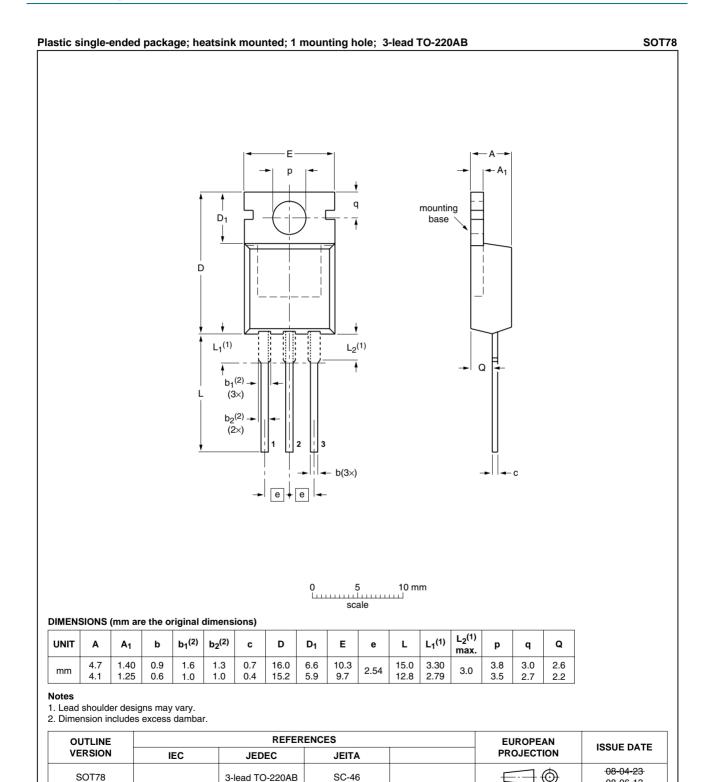
Fig 5. Reverse recovery definitions; ramp recovery

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Package outline



Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV410-600_1	20090629	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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